

FRD MODULE 80A/200V

P2H80F2

FEATURES

- * Compatible with Isolated Base SOT227
- * Dual Separated Diodes
- * Ultra – Fast Recovery
- * Low Forward Voltage Drop
- * High Surge Capability

OUTLINE DRAWING

See the Next Page

TYPICAL APPLICATIONS

- * High Frequency Rectification

Maximum Ratings

Approx Net Weight:35g

Parameter	Symbol	Type / Grade		Unit
		P2H80F2	-	
Repetitive Peak Reverse Voltage *1	V _{RRM}	200	-	V
Non Repetitive Peak Reverse Voltage *1	V _{RSM}	-	-	

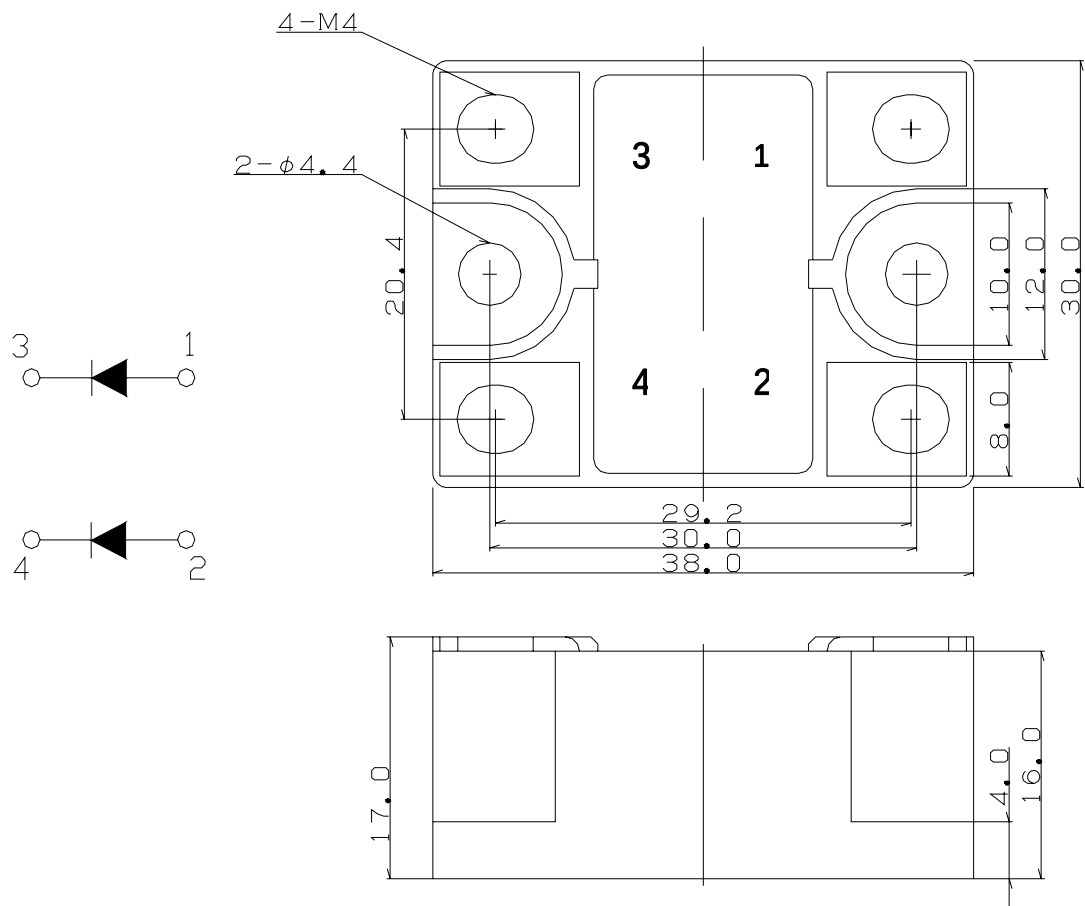
Parameter		Conditions	Max Rated Value	Unit
Average Rectified Output Current *1	I _{O(AV)}	50Hz Half Sine Wave condition T _c =96°C	80	A
RMS Forward Current *1	I _{F(RMS)}		125	A
Surge Forward Current *1	I _{FSM}	50 Hz Half Sine Wave,1Pulse Non-repetitive	800	A
I Squared t *1	I ² t	2msec to 10msec	3200	A ² s
Operating JunctionTemperature Range	T _{jw}		-40 to +150	°C
Storage Temperature Range	T _{stg}		-40 to +125	°C
Isoration Voltage	Viso	Base Plate to Terminals, AC1min	2500	V
Mounting torque	Case mounting	F _{tor}	M4Screw	N•m
	Terminals		M4Screw	

Electrical • Thermal Characteristics

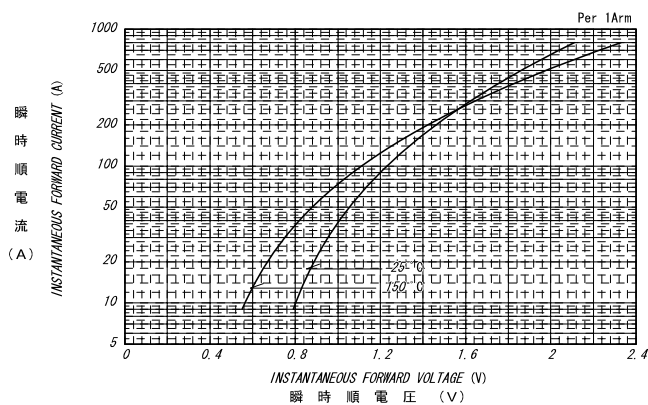
Characteristics	Symbol	Test Conditions	Max.	Unit
Peak Reverse Current *1	I _{RM}	V _{RM} = V _{RRM} , T _j = 25°C	75	μA
Peak Forward Voltage *1	V _{FM}	I _{FM} = 80A, T _j =25°C	1.05	V
Reverse Recovery Time	trr	T _j =25°C , I _{FM} =10A, -di/dt=50A/μs	50	ns
Thermal Resistance *1	R _{th(j-c)}	Junction to Case	0.51	°C/W
	R _{th(c-f)}	Base Plate to Heat Sink with Thermal Compound	0.3	

*1: Value Per 1Arm

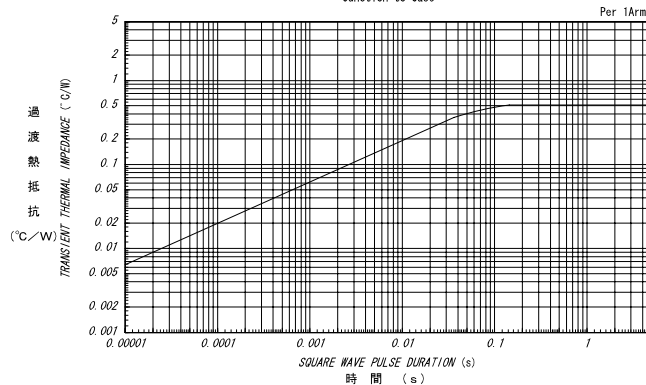
P2H80F2 OUTLINE DRAWING (Dimensions in mm)



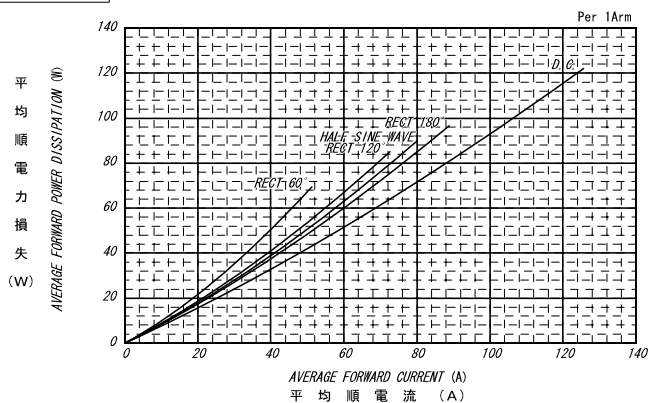
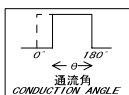
順電圧特性
FORWARD CURRENT VS. VOLTAGE



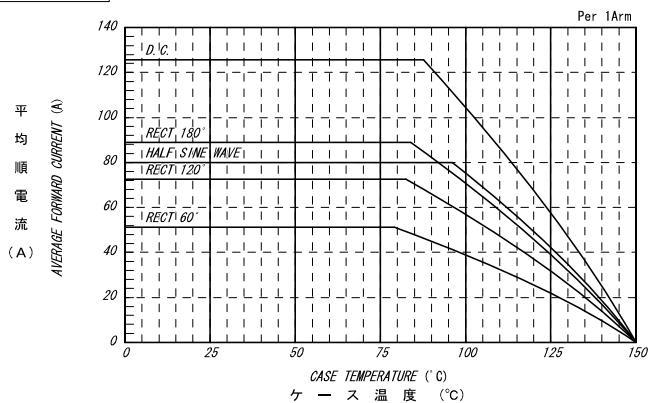
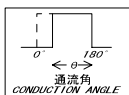
過渡熱抵抗特性
MAXIMUM TRANSIENT THERMAL IMPEDANCE
Junction to Case



平均順電力損失特性
AVERAGE FORWARD POWER DISSIPATION



平均順電流－ケース温度定格
AVERAGE FORWARD CURRENT VS. CASE TEMPERATURE



サージ順電流定格
SURGE CURRENT RATINGS

f=50Hz, Half Sine Wave, Non-Repetitive, No Load

